Quad Array for ESD Protection

NZQA5V6XV5T1G Series

This quad monolithic silicon voltage suppressor is designed for applications requiring transient overvoltage protection capability. It is intended for use in voltage and ESD sensitive equipment such as computers, printers, business machines, communication systems, medical equipment, and other applications. Its quad junction common anode design protects four separate lines using only one package. These devices are ideal for situations where board space is at a premium.

Specification Features

- SOT-553 Package Allows Four Separate Unidirectional Configurations
- Low Leakage < 1 μA @ 3 V for NZQA5V6XV5T1G
- Breakdown Voltage: 5.6 V – 6.8 V @ 1 mA
- ESD Protection Meeting IEC61000-4-2 – Level 4
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These are Pb-Free Devices

Mechanical Characteristics

- Void Free, Transfer-Molded, Thermosetting Plastic Case
- Corrosion Resistant Finish, Easily Solderable
- Package Designed for Optimal Automated Board Assembly
- Small Package Size for High Density Applications
- 100% Lead Free, MSL1 @ 260 °C Reflow Temperature

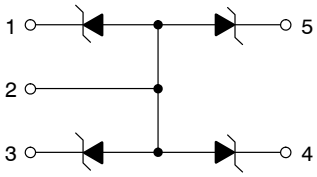


SOT-553
CASE 463B

MARKING DIAGRAM



xx = Specific Device Code
M = Date Code
▪ = Pb-Free Package
(Note: Microdot may be in either location)



ORDERING INFORMATION

See detailed ordering, marking, and shipping information on page 3 of this data sheet.

NOTE: Some of the devices on this data sheet have been **DISCONTINUED**. Please refer to the table on page 3.

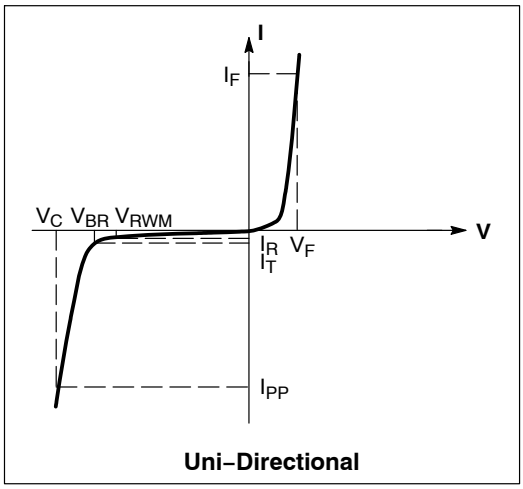
© Semiconductor Components Industries, LLC, 2014

Downloaded from Arrow.com.

ELECTRICAL CHARACTERISTICS

(T_A = 25 °C unless otherwise noted)

Symbol	Parameter
I_{PP}	Maximum Reverse Peak Pulse Current
V_C	Clamping Voltage @ I_{PP}
V_{RWM}	Working Peak Reverse Voltage
I_R	Maximum Reverse Leakage Current @ V_{RWM}
V_{BR}	Breakdown Voltage @ I_T
I_T	Test Current
ΘV_{BR}	Maximum Temperature Coefficient of V_{BR}
I_F	Forward Current
V_F	Forward Voltage @ I_F
Z_{ZT}	Maximum Zener Impedance @ I_{ZT}
I_{ZK}	Reverse Current
Z_{ZK}	Maximum Zener Impedance @ I_{ZK}



Uni−Directional

MAXIMUM RATINGS (T_A = 25 °C unless otherwise noted)

Characteristic	Symbol	Value	Unit
Peak Power Dissipation (8 X 20 μs @ T_A = 25 °C) (Note 1)	P_{PK}	100	W
Steady State Power − 1 Diode (Note 2)	P_D	300	mW
Thermal Resistance Junction to Ambient Above 25 °C, Derate	$R_{\theta JA}$	370 2.7	°C/W mW/°C
Maximum Junction Temperature	T_{Jmax}	150	°C
Operating Junction and Storage Temperature Range	T_J T_{stg}	−55 to +150	°C
ESD Discharge MIL STD 883C − Method 3015−6 IEC1000-4-2, Air Discharge IEC1000-4-2, Contact Discharge	V_{PP}	 16 30 30	 kV
Lead Solder Temperature (10 seconds duration)	T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ELECTRICAL CHARACTERISTICS (T_A = 25 °C)

Device*	Device Marking	Breakdown Voltage V_{BR} @ 1 mA (Volts)			Leakage Current I_{RM} @ V_{RM}		V_C Max @ I_{PP}		Typ Capacitance @ 0 V Bias (Note 3)	Max V_F @ I_F = 200 mA
		Min	Nom	Max	V_{RWM}	I_{RWM} (μA)	V_C (V)	I_{PP} (A)	(pF)	(V)
NZQA5V6XV5T1G	56	5.32	5.6	5.88	3.0	1.0	10.5	10	90	1.3
NZQA6V2XV5T1G	62	5.89	6.2	6.51	4.0	0.5	11.5	9.0	80	1.3
NZQA6V8XV5T1G	68	6.46	6.8	7.14	4.3	0.1	12.5	8.0	70	1.3

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

* Includes SZ-prefix devices where applicable.

1. Non-repetitive current per Figure 1.
2. Only 1 diode under power. For all 4 diodes under power, P_D will be 25%. Mounted on FR-4 board with min pad.
3. Capacitance of one diode at f = 1 MHz, V_R = 0 V, T_A = 25 °C

Share Feedback
Your Opinion Matters

Downloaded from Arrow.com.

TYPICAL CHARACTERISTICS

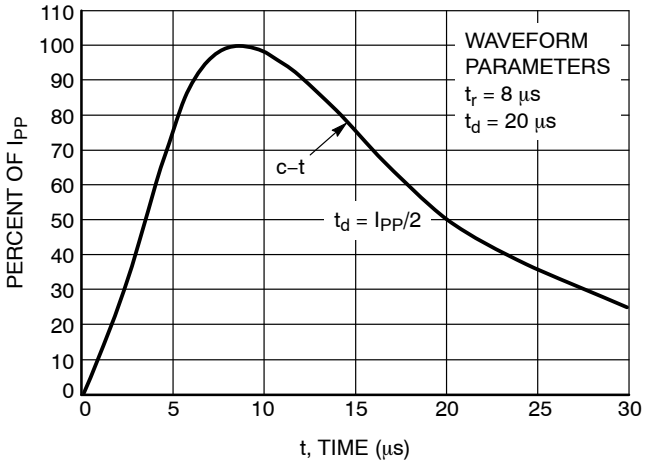


Figure 1. Pulse Waveform

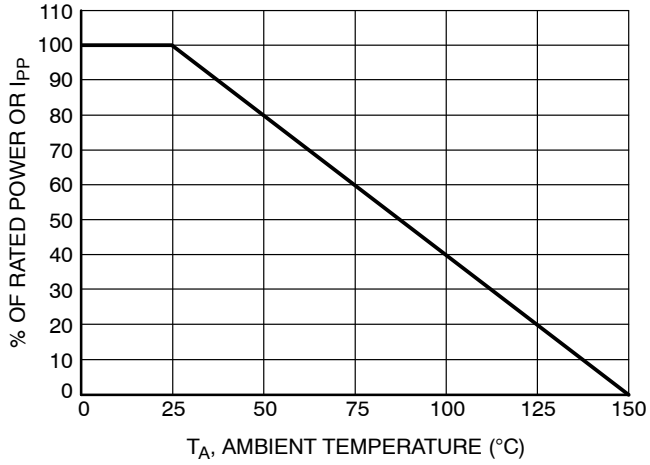


Figure 2. Power Derating Curve

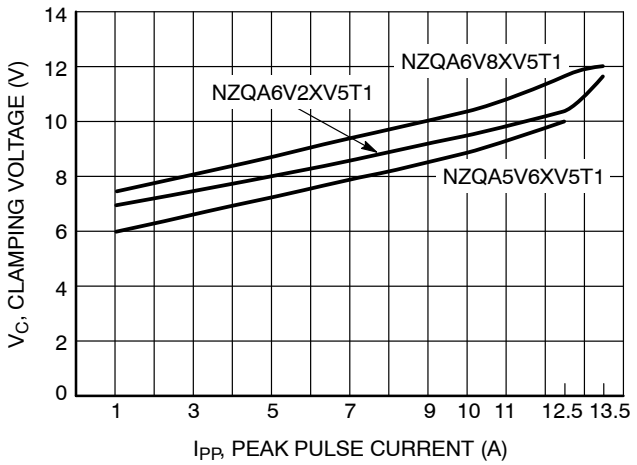


Figure 3. Clamping Voltage versus Peak Pulse Current

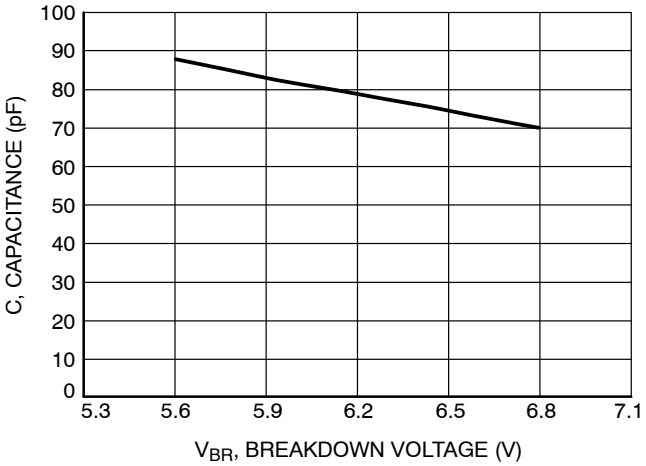


Figure 4. Typical Capacitance

Table 1. ORDERING INFORMATION

Device	Package	Shipping†
NZQA5V6XV5T1G	SOT-553 (Pb-Free)	4000 / Tape & Reel
NZQA6V2XV5T1G		
NZQA6V8XV5T1G		

DISCONTINUED (Note 4)

NZQA5V6XV5T3G	SOT-553 (Pb-Free)	16000 / Tape & Reel
SZQA6V8XV5T1G		

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

4. **DISCONTINUED:** These devices are not available. Please contact your **onsemi** representative for information. The most current information on these devices may be available on www.onsemi.com.

Share Feedback
Your Opinion Matters

Downloaded from Arrow.com.

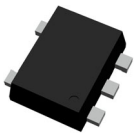
REVISION HISTORY

Revision	Description of Changes	Date
6	Rebranded the Data Sheet to **onsemi** format. NZQA5V6XV5T3G, SZQA6V8XV5T1G OPNs Marked as Discontinued.	2/26/2026

This document has undergone updates prior to the inclusion of this revision history table. The changes tracked here only reflect updates made on the noted approval dates.

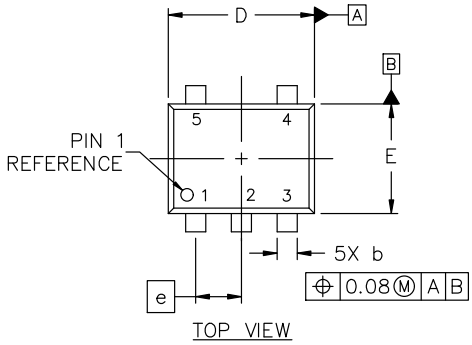
Share Feedback
Your Opinion Matters

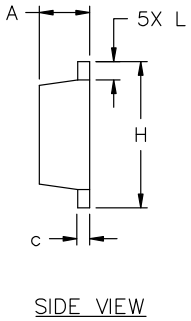
Downloaded from Arrow.com.



SOT−553−5 1.60x1.20x0.55, 0.50P
CASE 463B
ISSUE D

DATE 21 FEB 2024

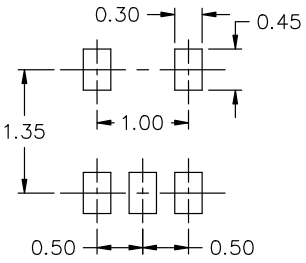




NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5−2018.
2. ALL DIMENSION ARE IN MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.50	0.55	0.60
b	0.17	0.22	0.27
c	0.08	0.13	0.18
D	1.55	1.60	1.65
E	1.15	1.20	1.25
e	0.50 BSC		
H	1.55	1.60	1.65
L	0.10	0.20	0.30



RECOMMENDED MOUNTING FOOTPRINT*

* FOR ADDITIONAL INFORMATION ON OUR Pb−FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:
PIN 1. BASE
2. EMITTER
3. BASE
4. COLLECTOR
5. COLLECTOR

STYLE 2:
PIN 1. CATHODE
2. COMMON ANODE
3. CATHODE 2
4. CATHODE 3
5. CATHODE 4

STYLE 3:
PIN 1. ANODE 1
2. N/C
3. ANODE 2
4. CATHODE 2
5. CATHODE 1

STYLE 4:
PIN 1. SOURCE 1
2. DRAIN 1/2
3. SOURCE 1
4. GATE 1
5. GATE 2

STYLE 5:
PIN 1. ANODE
2. EMITTER
3. BASE
4. COLLECTOR
5. CATHODE

STYLE 6:
PIN 1. EMITTER 2
2. BASE 2
3. EMITTER 1
4. COLLECTOR 1
5. COLLECTOR 2/BASE 1

STYLE 7:
PIN 1. BASE
2. EMITTER
3. BASE
4. COLLECTOR
5. COLLECTOR

STYLE 8:
PIN 1. CATHODE
2. COLLECTOR
3. N/C
4. BASE
5. EMITTER

STYLE 9:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. ANODE
5. ANODE

DOCUMENT NUMBER:	**98AON11127D**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.
DESCRIPTION:	**SOT−553−5 1.60x1.20x0.55, 0.50P**	**PAGE 1 OF 1**

onsemi and onsemi are trademarks of Semiconductor Components Industries, LLC dba **onsemi** or its subsidiaries in the United States and/or other countries. **onsemi** reserves the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

Downloaded from Arrow.com.

onsemi, ONSEMI , and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent−Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as−is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical−documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support
For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales

◊

Downloaded from Arrow.com.